

	Hits	Search Text
1	6601	(resist photoresist) with ash\$3 (plasma near strip\$4) and (RF with (bias\$3 and (plasma source)))
2	207	(resist photoresist) with (ash\$3 (plasma near strip\$4)) and (RF with (bias\$3 and (plasma source)))
3	194	2 and (oxygen ozone 03 02 "0.sub.3" "0.sub.2")
4	99	3 and ((oxygen ozone 03 02 "0.sub.3" "0.sub.2") with (N2 "N.sub.2" CF4 "CF.sub.4"))
5	18	4 and ratio with (bias power RF W watt)
6	6	5 and (low adj (k dielectric) low-k BCB SiLK parylene HSQ polyarylene)
7	0	7 and 8
8	5	2 and ratio near (bias power RF W watt)
9	52	2 and ((low adj (k dielectric) low-k BCB SiLK parylene HSQ polyarylene))
10	46	7 not (5 6 8)
11	4	2 and (increas\$3 chang\$3 degrad\$3 reduc\$3 decreas\$3 damag\$3 destroy\$3) near (low adj (k dielectric) "low-k" low-k)
12	17	2 and (increas\$3 chang\$3 degrad\$3 reduc\$3 decreas\$3 damag\$3 destroy\$3) with (low adj (k dielectric) "low-k" low-k)
13	27	2 and (increas\$3 chang\$3 degrad\$3 reduc\$3 decreas\$3 damag\$3 destroy\$3) same (low adj (k dielectric) "low-k" low-k)
14	12	2 and (increas\$3 chang\$3 degrad\$3 reduc\$3 decreas\$3 damag\$3 destroy\$3) same (low adj (k dielectric) "low-k" low-k) same (ash\$3 resist photoresist)

	DBs
1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
2	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
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13	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
14	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB